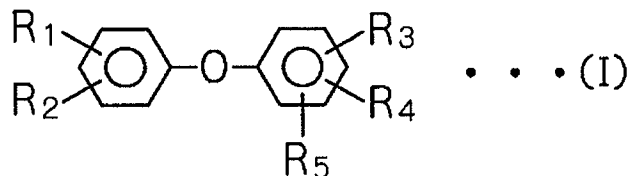


LISTING OF CLAIMS
(no amendments have been made)

1. **(Previously presented)** A developer composition for resists, comprising an organic quaternary ammonium base as a main component and a surfactant,

said surfactant containing an anionic surfactant represented by the following general formula (I):



wherein at least one member of R₁ and R₂ represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any remaining member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of R₃, R₄ and R₅ represents a group represented by the following general formula (II):



wherein M represents a metal atom, and any remaining member represent a hydrogen atom or a group represented by the above general formula (II).

2. **(Original)** The developer composition for resists according to claim 1, wherein, in the general formula (II), M represents one selected from sodium, potassium and calcium, provided that, in the general formula (I), when two or more groups represented by the general formula (II) are present, M may be the same or different.

3. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

4. **(Previously presented)** A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 2 to form a resist pattern.